

REMARKS

Applicants appreciate the early indication of allowability as to claims 12-14 of the application. The specification is amended herein to correct the informalities noted by the Examiner, as well as to clarify that which reference numeral 700 indicates, namely the surface of the substrate. Accordingly, the objection to FIG. 7 is obviated by the amendment to the Specification presented herein. No new matter is introduced by the changes to the drawings and the Specification herein.

In the Office Action, claims 1-11 were rejected under 35 U.S.C. §103(a) as being obvious over U.S. Patent No. 6,534,352 B1 to Kim ("*Kim*") in view of U.S. Patent No. 6,300,206 B1 to Fukada ("*Fukada*"). For the reasons set forth below, Applicants respectfully submit that the claims as amended herein fully overcome the rejections made over *Kim* in view of *Fukada*.

As now recited in amended claim 1, a method of fabricating a field effect transistor includes forming a metal gate structure which includes a first conductive layer that is separated from a substrate only by a thickness of a gate dielectric of the transistor.

Clearly, neither *Kim* nor *Fukada* teach or suggest this feature of the presently recited invention. *Kim* merely describes a MOSFET fabrication method in which dielectric spacers 33 of silicon nitride, not conductive spacers, are formed on sidewalls of an opening formerly occupied by a sacrificial gate, and where the spacers 33 contact the gate dielectric 36. Further, the spacers are not separated from a transistor channel region only by a thickness of a gate dielectric. Rather, as shown in FIG. 2F, the spacers 33 are separated from the transistor channel region by the thickness of the source and drain regions 34.

Moreover, *Fukada* merely describes a conventional method of forming a

layer of silicide overlying a polysilicon layer of a gate. *Fukada* fails to teach forming a layer of silicide to overlie a first conductive layer which includes one or more materials selected from metals and compounds of metals.


Support for the present amendments is provided, *inter alia*, in the portions of the specification relating to FIGS. 3-7 and 8-13.

In view of the foregoing amendments and remarks, Applicants submit that the application is now in condition for immediate allowance. If for any reason the Examiner has any question regarding the content of this amendment or the allowability of the presently pending claims, he is respectfully requested to contact the Applicants' undersigned attorney at the telephone number indicated below.

It is believed that no fee is required upon filing this Amendment. However, if any fee is required, authorization is given to debit the Deposit Account No. 09-0458 of the Assignee for the amount due, and to credit any overpayment to the same account.

Respectfully submitted,
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